Amendments to the Specification

Please replace the abstract with the following amended abstract:

In a method of manufacturing a nonvolatile semiconductor storage device, an element isolation region ~~(12 in Fig. 1)~~ is formed in a semiconductor substrate [[(11)]], a tunnel oxide film [[(13)]] and a polysilicon layer ~~to become a floating gate (14) later~~ are successively formed on the ~~resulting~~ semiconductor substrate, and nitrogen ions are thereafter implanted into the front surface of the polysilicon layer so as to stay in the ~~only this~~ front surface only. The polysilicon layer is patterned to form [[the]] a floating gate [[(14)]], ~~and this floating gate (14)~~ which is then thermally oxidized to form an inter-gate insulating film [[(15)]]. Since [[the]] thermal oxidation is suppressed by [[the]] nitrogen ions, the inter-gate insulating film ~~(15) can be made~~ is thicker at the side surfaces of the floating gate [[(14)]] than at the front surface ~~thereof~~. ~~Thus, the~~ The inter-gate insulating film [[(15)]] at the edge [[part]] of the floating gate [[(14)]] can be formed as designed, so that the ~~nonvolatile semiconductor~~ storage device is free from bad influence ~~on its~~ during electrical programming and erasing, and ~~is capable of retaining charges for a long time~~ can retain charge longer.